

**IN THE CLAIMS:**

The following is a complete listing of claims in this application.

Claims 1-12 (canceled).

13. (currently amended) Method for constructing a an electrically conducting linear and/or punctiform structure on a support, comprising the steps of:

applying to a portion of the support a flowable, electrically conductive paste-like substance containing a solvent in a linear or punctiform arrangement;

after said applying, contacting the substance with a medium containing a polar molecule, causing thereby the solvent contained in the substance to be extracted therefrom in an edge region, resulting in a hardening and stabilizing of the substance in the edge region.

14. (previously presented) Method according to claim 13, wherein the support comprises a semiconductor solar cell.

15. (previously presented) Method according to claim 13, wherein the polar medium comprises water or a mixture of water and at least one surfactant selected from the group consisting of anionic surfactants, cationic surfactants, non-ionic surfactants, and amphoteric surfactants.

16. (previously presented) Method according to claim 15, wherein the surfactants are selected from the group consisting of soap, fatty alcohol sulfates, alkyl benzene sulfonates, non-carbonic acid ester of polyalcohols.

17. (previously presented) Method according to claim 13, wherein the paste-like substance is applied to the support by at least one of screen printing, tampon printing, finger writing techniques or spraying techniques.

18. (previously presented) Method according to claim 13, wherein the polar medium is applied to the substance from about 0.1 to about 600 seconds after applying the substance to

the support.

19. (previously presented) Method according to claim 18, wherein the polar medium is applied to the substance from about 1 to about 60 seconds after applying the substance to the support.

20. (previously presented) Method according to claim 13, wherein the substance is applied to the support in a circular cross section with a diameter  $d$ , where about  $15\text{ }\mu\text{m} \leq d \leq$  about  $300\text{ }\mu\text{m}$ .

21. (previously presented) Method according to claim 20, wherein  $d$  is about  $80\text{ }\mu\text{m}$ .

22. (previously presented) Method according to claim 13, wherein the substance includes water soluble and water insoluble solvents.

23. (previously presented) Method according to claim 13, wherein the substance is applied to the substrate such that after hardening, the substance has a height to breadth ratio  $a$ , where  $0.1 \leq a \leq 1.0$ .

24. (previously presented) Method according to claim 23, where  $a$  is about 0.3.

25. (previously presented) Method according to claim 13, wherein the support is a silicon substrate with a surface layer comprising at least one of silicon oxide and silicon nitride.

26. (previously presented) Method according to claim 13, wherein a concentration gradient between the polar medium and the substance is set with respect to the solvents present in the substance, such that the solvent of the substance is extracted into the medium.

27. (currently amended) Method for constructing a an electrically conducting linear and/or punctiform structure on a support, comprising the steps of:

applying to a portion of the support a flowable,

electrically conductive paste-like substance containing a solvent in a linear or punctiform arrangement;

after said applying, contacting the support with a medium containing a polar molecule, with forces of adhesion between the medium and the support being greater than forces of adhesion between the substance and the support,

said contacting thereby substantially preventing flowing of the substance along the support and detachment of the substance from the support.

28. (previously presented) Method according to claim 27, wherein the polar medium is applied on the support in the form of a liquid or a foam in the region of the applied paste-like substance.

29. (previously presented) Method according to claim 28, wherein the polar medium comprises water or a mixture of water and at least one surfactant selected from the group consisting of anionic surfactants, cationic surfactants, non-ionic surfactants, and amphoteric surfactants.

30. (previously presented) Method according to claim 29, wherein the surfactants are selected from the group consisting of soap, fatty alcohol sulfates, alkyl benzene sulfonates, non-carbonic acid ester of polyalcohols.

31. (previously presented) Method according to claim 27, wherein the paste-like substance is applied to the support by at least one of screen printing, tampon printing, finger writing techniques or spraying techniques.

32. (previously presented) Method according to claim 27, wherein the polar medium is applied to the substance from about 0.1 to about 600 seconds after applying the substance to the support.

33. (previously presented) Method according to claim 32, wherein the polar medium is applied to the substance from about 1 to about 60 seconds after applying the substance to

the support.

34. (previously presented) Method according to claim 27, wherein the substance is applied to the support in a circular cross section with a diameter  $d$ , where about  $15\text{ }\mu\text{m} \leq d \leq$  about  $300\text{ }\mu\text{m}$ .

35. (previously presented) Method according to claim 34, wherein  $d$  is about  $80\text{ }\mu\text{m}$ .

36. (previously presented) Method according to claim 27, wherein the substance includes water soluble and water insoluble solvents.

37. (previously presented) Method according to claim 27, wherein the substance is applied to the substrate such that after hardening, the substance has a height to breadth ratio  $a$ , where  $0.1 \leq a \leq 1.0$ .

38. (previously presented) Method according to claim 37, where  $a$  is about  $0.3$ .

39. (previously presented) Method according to claim 27, wherein the support comprises a semiconductor solar cell.

40. (previously presented) Method according to claim 27, wherein the support is a silicon substrate with a surface layer comprising at least one of silicon oxide and silicon nitride.